Low Vcesat NPN Epitaxial Planar Transistor

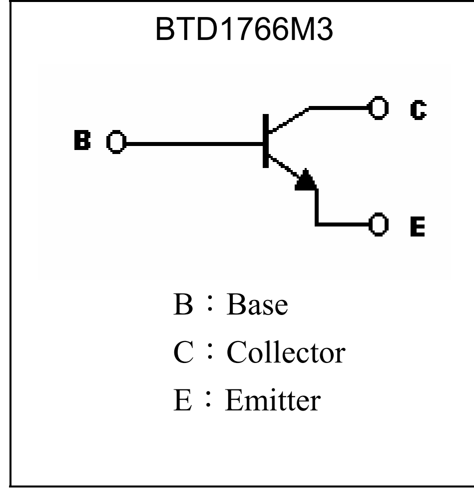
BTD1766M3

BV_{CEO}	32V
I_C	2A
R_{CESAT}(typ)	150mΩ

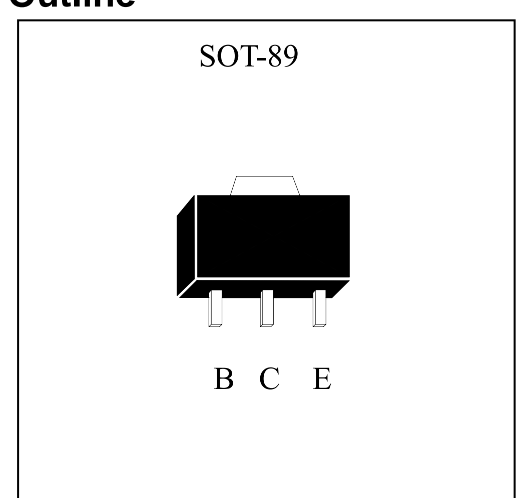
Features

- Low V_{CE}(sat), 0.3V typ. at I_C / I_B = 2A / 0.2A
- Excellent current gain characteristics
- Complementary to BTB1188M3
- Pb-free lead plating and halogen-free package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	32	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse)	I_{CP}	4	A
Power Dissipation	P_D	0.6	W
		1 (Note 1)	
		2 (Note 2)	
Operating Junction and Storage Temperature Range	Tj ; Tstg	-55~+150	°C

Note : 1. When mounted on FR-4 PCB with area measuring 10×10×1 mm
2. When mounted on ceramic with area measuring 40×40×1 mm

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	208	°C/W
		125 (Note 1)	
		62.5 (Note 2)	

Note : 1. When mounted on FR-4 PCB with area measuring 10×10×1 mm
2 . When mounted on ceramic with area measuring 40×40×1 mm

Characteristics (Ta=25°C)

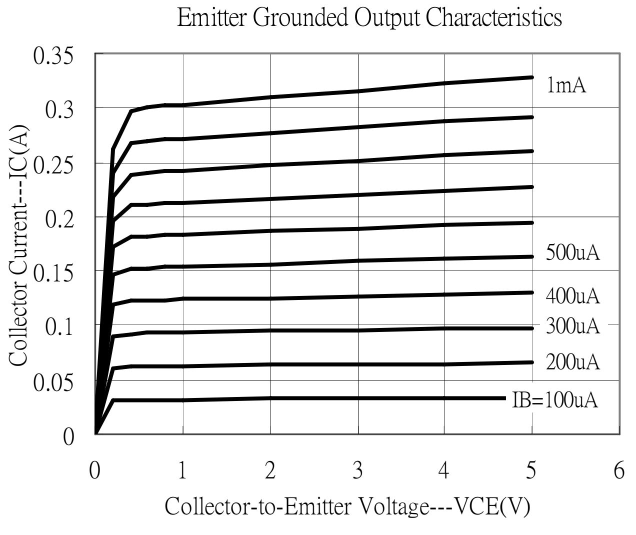
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	60	-	-	V	I_C=50μA, I_E=0
BV_{CEO}	32	-	-	V	I_C=1mA, I_B=0
BV_{EBO}	6	-	-	V	I_E=50μA, I_C=0
I_{CBO}	-	-	100	nA	V_{CB}=60V, I_E=0
I_{EBO}	-	-	100	nA	V_{EB}=6V, I_C=0
*$V_{CE(sat)}$	-	0.3	0.5	V	I_C=2A, I_B=0.2A
*$R_{CE(sat)}$	-	0.15	0.25	Ω	I_C=2A, I_B=0.2A
*$V_{BE(sat)}$	-	-	1.5	V	I_C=2A, I_B=0.2A
*$h_{FE}1$	160	-	-	-	V_{CE}=3V, I_C=20mA
*$h_{FE}2$	180	-	390	-	V_{CE}=3V, I_C=500mA
*$h_{FE}3$	150	-	-	-	V_{CE}=3V, I_C=1A
f_T	-	270	-	MHz	V_{CE}=5V, I_C=0.5A, f=100MHz
Cob	-	16	-	pF	V_{CB}=10V, f=1MHz

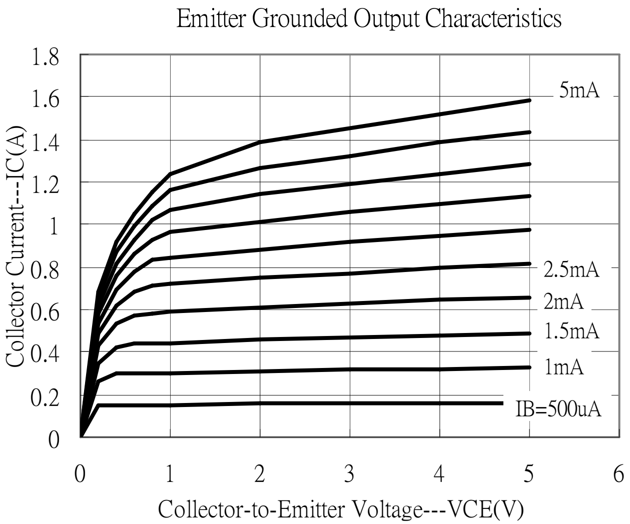
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

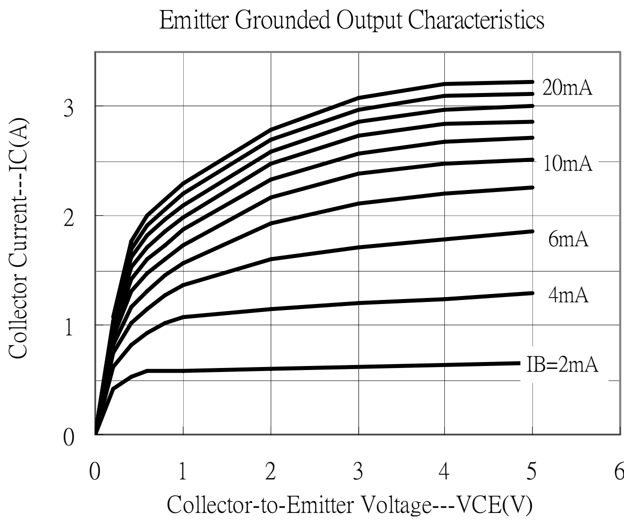
Ordering Information

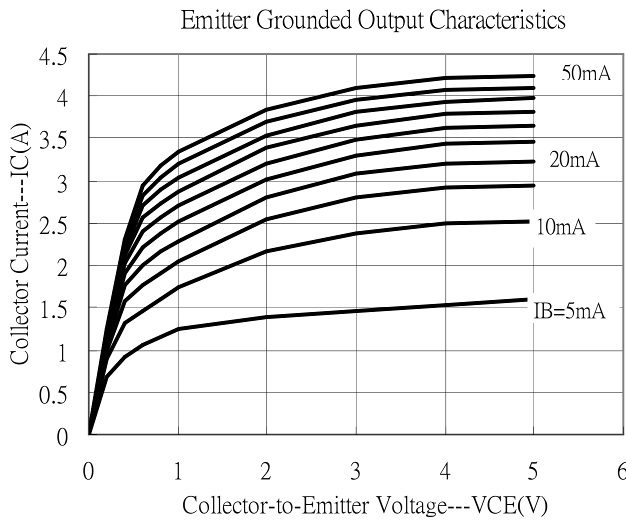
Device	Package	Shipping
BTD1766M3-0-T2-G	SOT-89 (Pb-free lead plating and halogen-free package)	1000 pcs / Tape & Reel

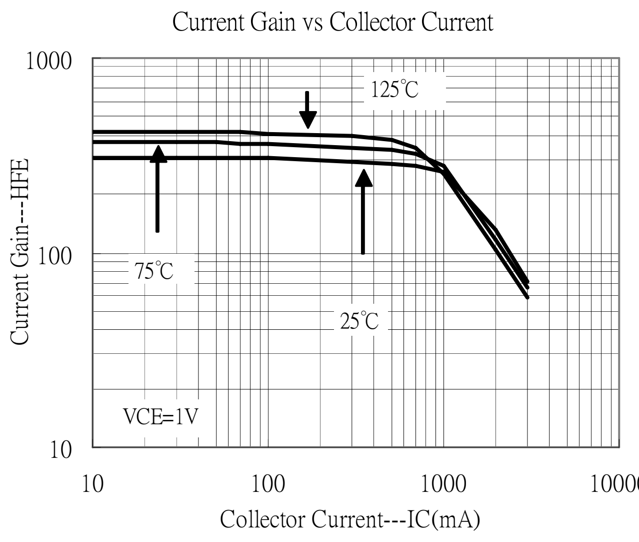
Typical Characteristics

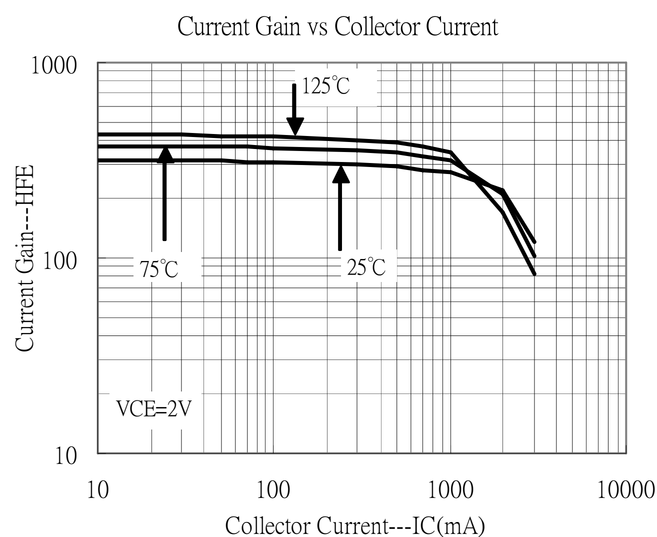




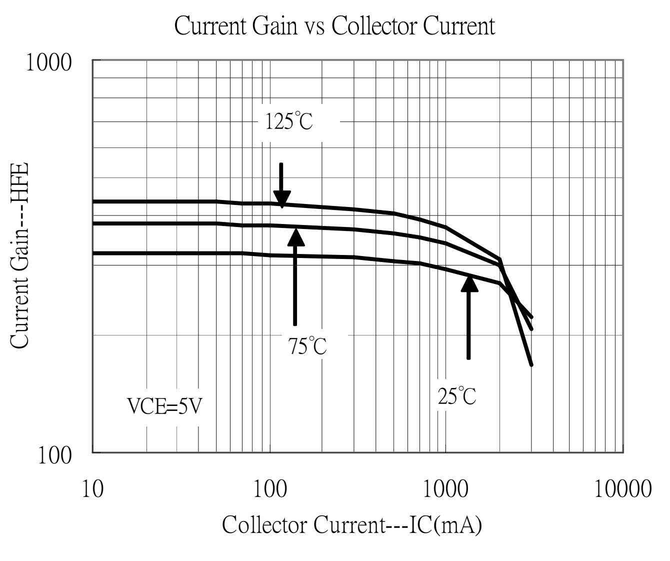


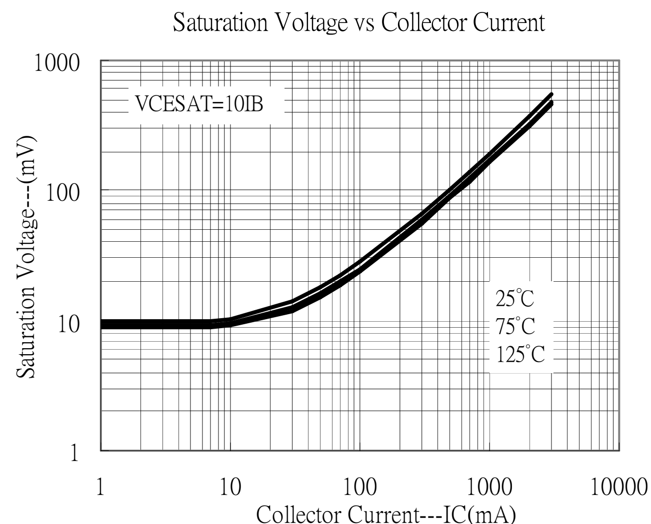


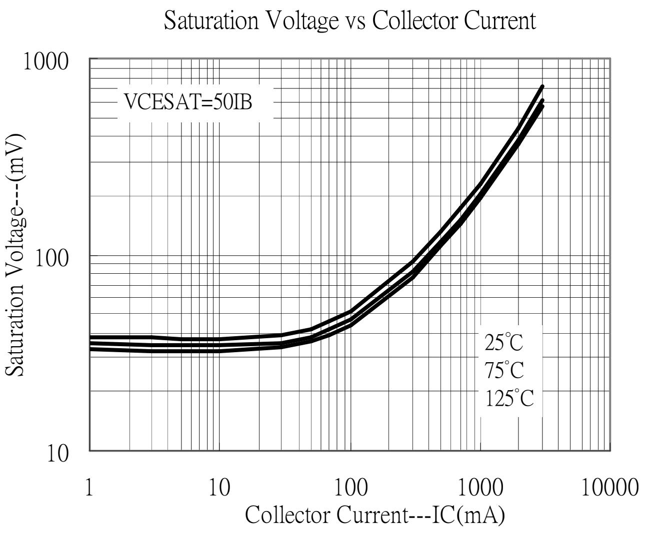


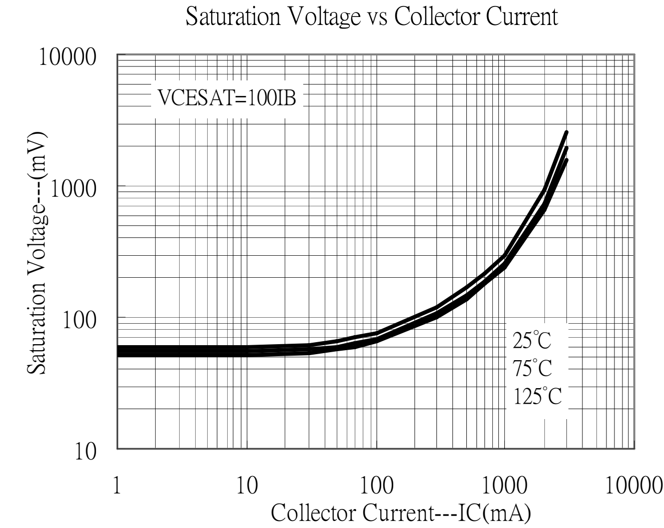


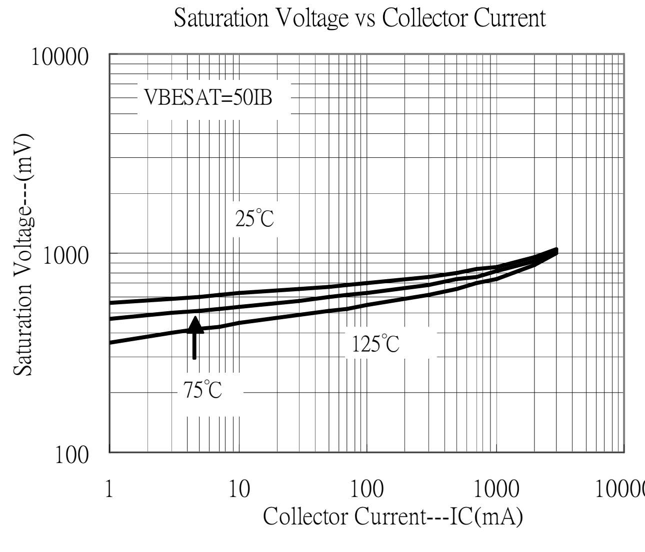
Typical Characteristics(Cont.)

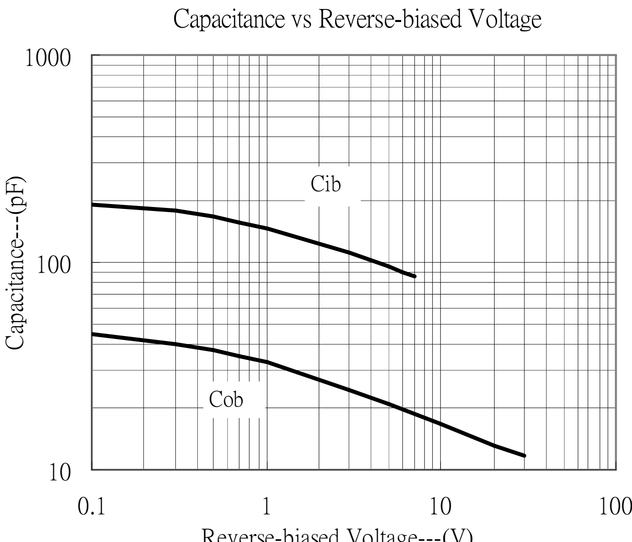




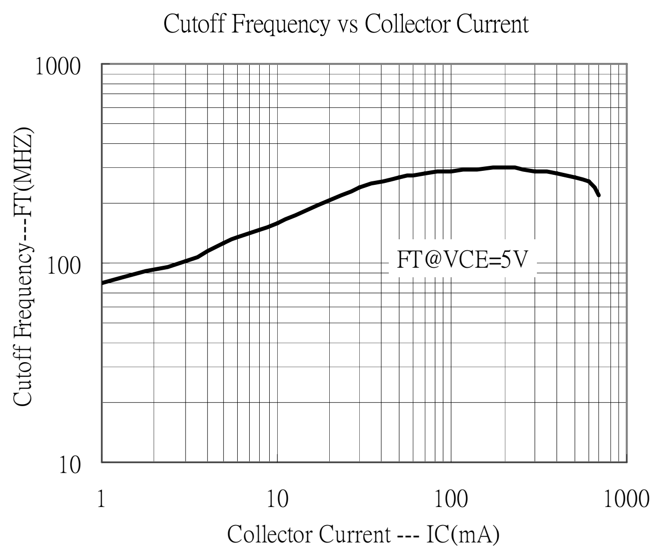


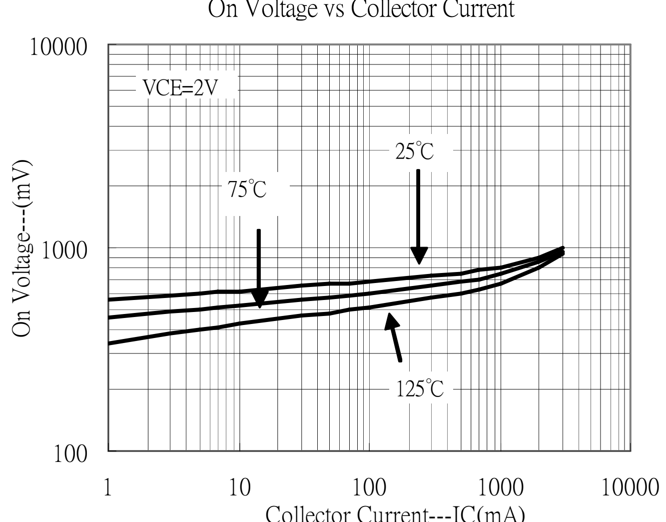


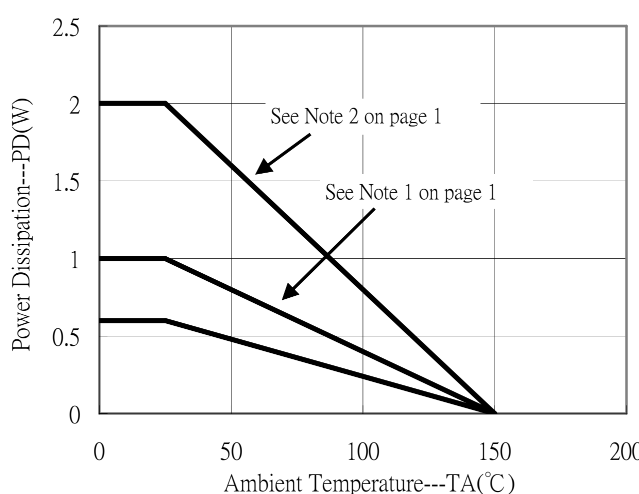




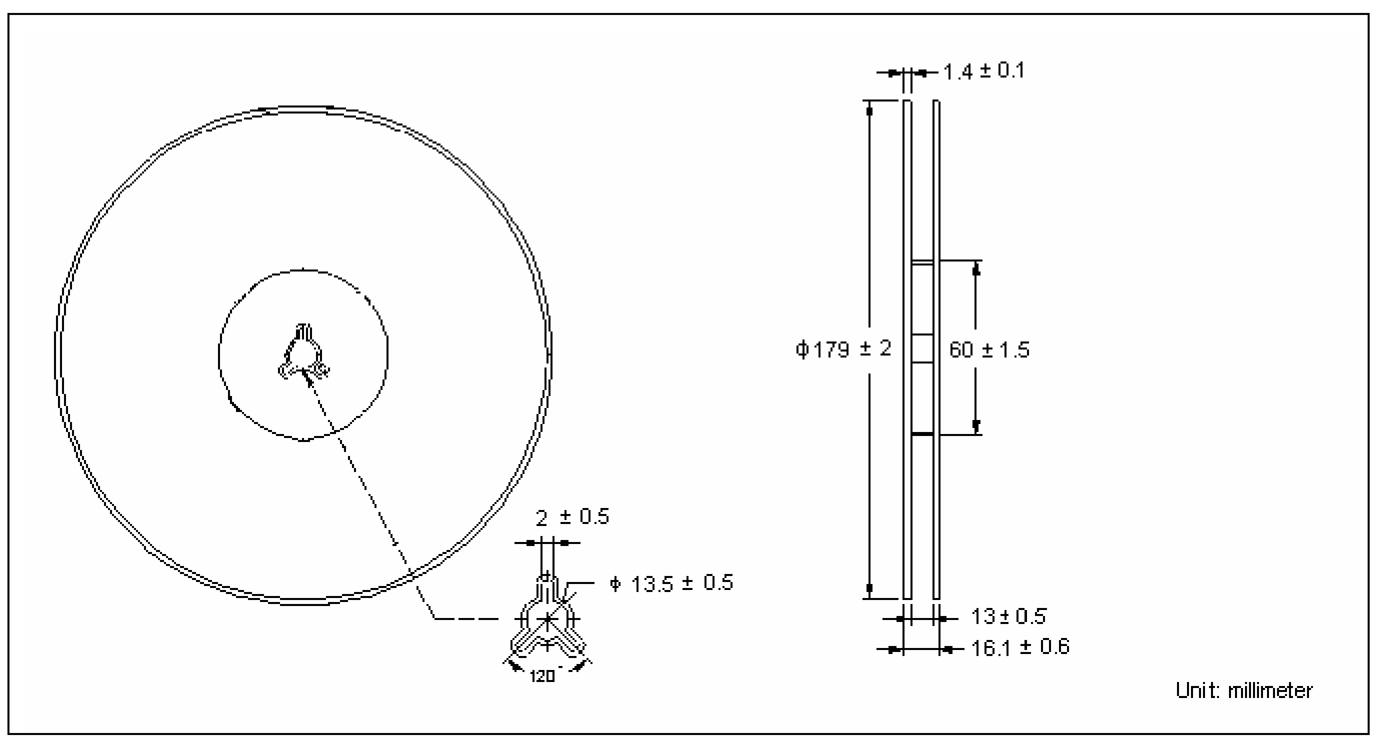
Typical Characteristics(Cont.)



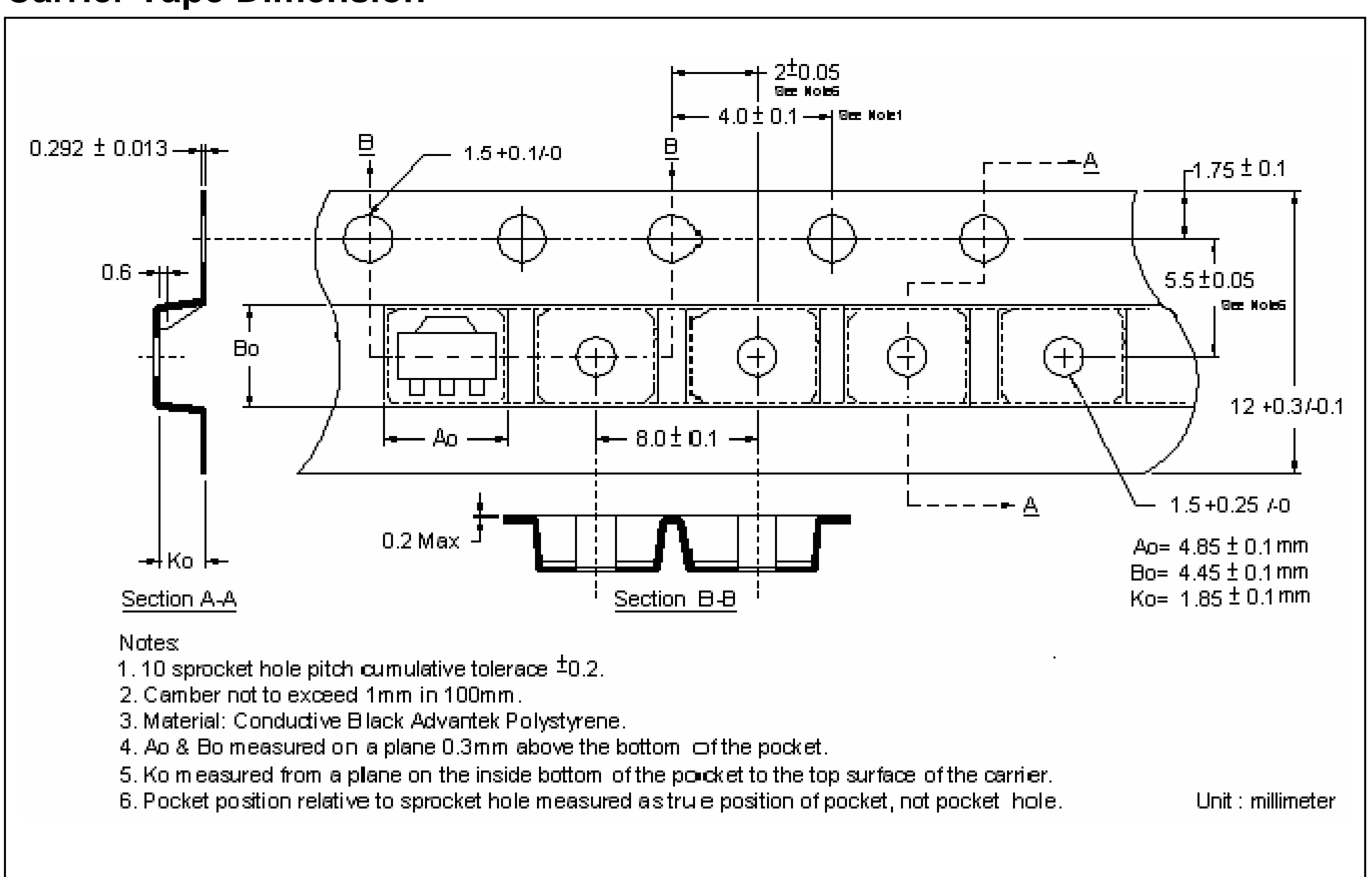




Reel Dimension



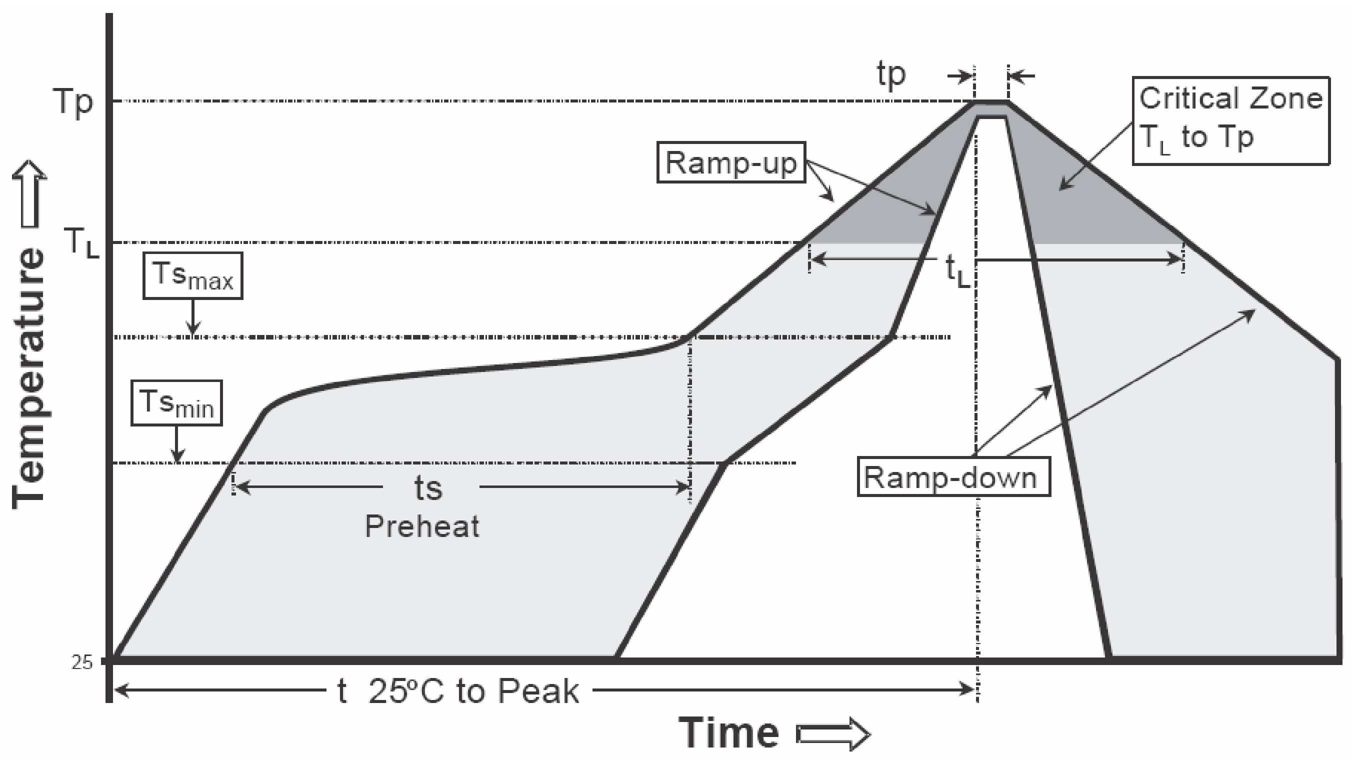
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

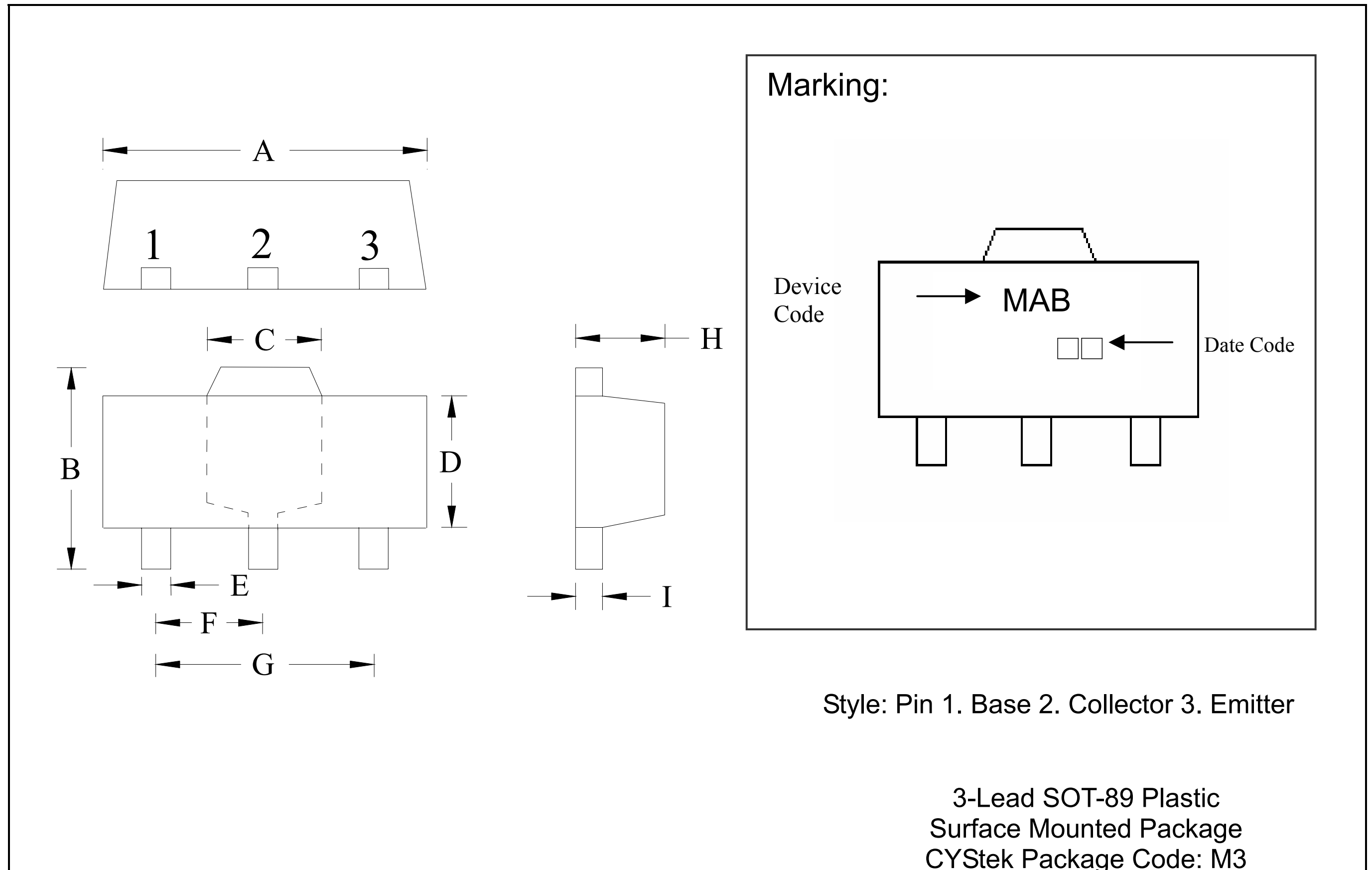
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(Ts min) −Temperature Max(Ts max) −Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (TL) − Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-89 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1732	0.1811	4.40	4.60	F	0.0591	TYP	1.50	TYP
B	0.1551	0.1673	3.94	4.25	G	0.1181	TYP	3.00	TYP
C	0.0610	REF	1.55	REF	H	0.0551	0.0630	1.40	1.60
D	0.0906	0.1024	2.30	2.60	I	0.0138	0.0173	0.35	0.44
E	0.0126	0.0205	0.32	0.52					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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